

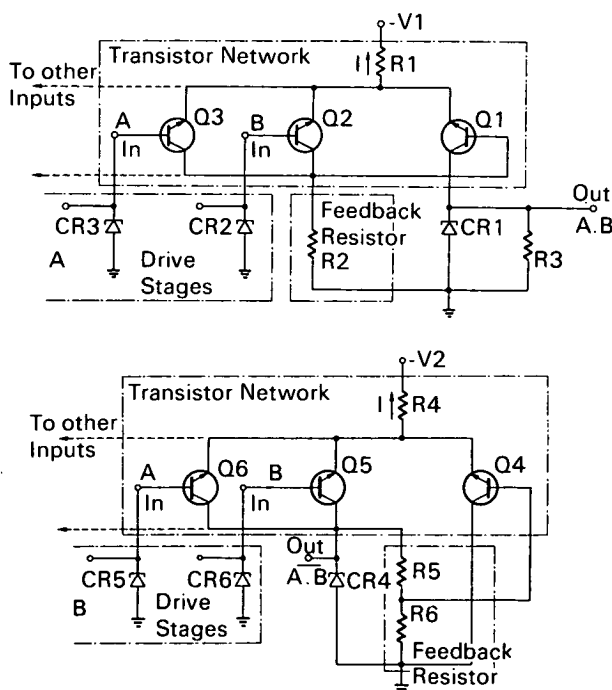
NASA TECH BRIEF



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Switching Circuits with Fast Response and Low Power Drain

A new family of logic circuits have response times no longer than 10 nanoseconds and drain only milliwatts of power. The family includes AND and NAND gates with their associated monostables, bistables, delays, and oscillators. The basic circuits form the basis of all logic functions; thus they can be used in various types of digital-data-processing systems.



Circuits of AND Gate (A) and NAND Gate (B)

The input signals of an AND circuit (Fig. 1A) are derived across tunnel diodes $CR2$ and $CR3$ and applied to transistors $Q2$ and $Q3$. The output is taken across $CR1$ which is connected to the voltage source

through $Q1$. Transistors $Q1$, $Q2$, and $Q3$ form a transistor network. In operation, when both driving tunnel diodes $CR2$ and $CR3$ are in their high-voltage state, both input transistors $Q2$ and $Q3$ are cut off. The resultant low voltage across $R2$, a series feedback resistor, allows $Q1$ to carry all current I . The collector current of $Q1$ now switches $CR1$ to its high-voltage state, creating a high voltage at the output terminal $A \cdot B$. When $CR2$ or $CR3$, one or both, is in the low-voltage state, its associated input transistor ($Q2$ or $Q3$) conducts all current I from $-V1$. The resultant voltage across series feedback resistor $R2$ is applied to the base of and cuts off $Q1$; thus no current flows through $CR1$ with the result that the output voltage is essentially zero. Thus this circuit provides an AND-gate logic function. Suitable choice of components can make the power drain on the gate ≤ 2 mW; the response time, ≤ 10 nanoseconds.

In a NAND gate (Fig. 1B) the input signals are taken across tunnel diodes $CR5$ and $CR6$ and applied to input transistors $Q5$ and $Q6$. The output is taken across $CR4$. A state of high-voltage output exists across $CR4$ whenever both driving tunnel diodes $CR5$ and $CR6$ are not in the high-voltage state; more specifically, when one or both are in a low-voltage state, the associated input transistor conducts current I . This conduction causes $CR4$ to be in its high-voltage state and generate an output signal. The voltage under this condition at the junction of $R5$ and $R6$, which form a series feedback resistor, is applied to the base of and cuts off $Q4$. However, when all the driving tunnel diodes are in the high-voltage state, none of the input transistors conducts and $CR4$ is in its low-voltage state; zero voltage at the junction of $R5$ and $R6$ allows $Q4$ to conduct all current I . Thus the circuit acts as a NAND gate.

(continued overleaf)

A circuit is provided having low output impedance and high input impedance whereby it can be used in a logic chain without need of coupling elements with their inherent disadvantages. Moreover the system operates from a single-level voltage source and has a substantially constant current drain, so that noise spikes and need for a multilevel-voltage source are eliminated.

Note:

Requests for further information may be directed to:

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Reference: TSP70-10250

Patent status:

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